优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)\ MAX}$	$I_{D\ MAX}$ T_A = +25°C
-30V	0.9Ω @ V_{GS} = -10V	-0.52A
	1.7Ω @ V_{GS} = -4.5V	-0.38A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

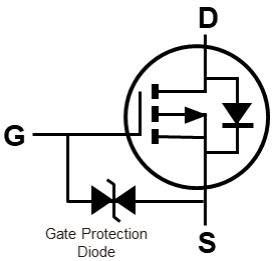
- DC-DC converters
- Load switches
- Power management functions

Mechanical Data

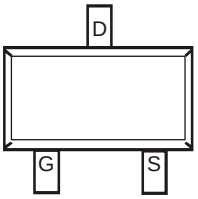
- Package: SOT323
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT323

Top View



Equivalent Circuit



Pin-Out
Top View

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T_A = +25°C	I_D	-0.38	A
		T_A = +70°C		-0.3	
Maximum Body Diode Forward Current (Note 5)			I_S	-0.42	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I_{DM}	-2.6	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_D	0.29	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	424	°C/W
Total Power Dissipation (Note 5)		P_D	0.37	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	334	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	μA	V_{DS} = -24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	-2.0	-2.6	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.45	0.9	Ω	V_{GS} = -10V, I_D = -0.42A
			0.74	1.7		V_{GS} = -4.5V, I_D = -0.2A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -0.23A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	19	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	16	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	3	—	pF	
Gate Resistance	R_g	—	729	—	Ω	V_{DS} = V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	0.36	—	nC	V_{GS} = -4.5V, V_{DS} = -10V I_D = -250mA
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	30	—	ns	V_{DD} = -10V, V_{GS} = -4.5V R_L = 47Ω, R_g = 10Ω I_D = -200mA
Turn-On Rise Time	t_R	—	74	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	28	—	ns	
Turn-Off Fall Time	t_F	—	31	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

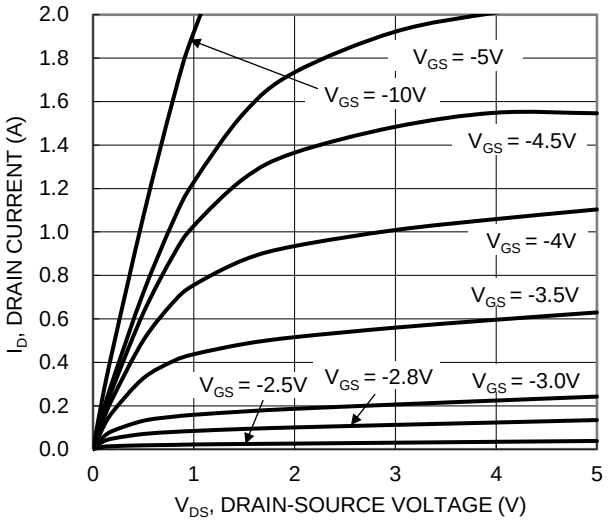


Figure 1. Typical Output Characteristic

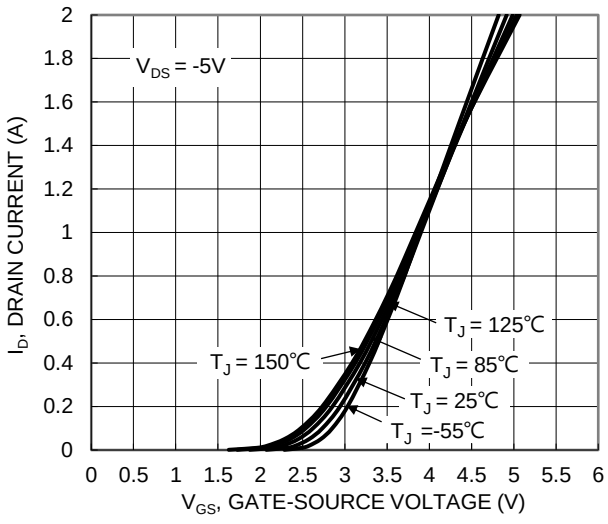


Figure 2. Typical Transfer Characteristic

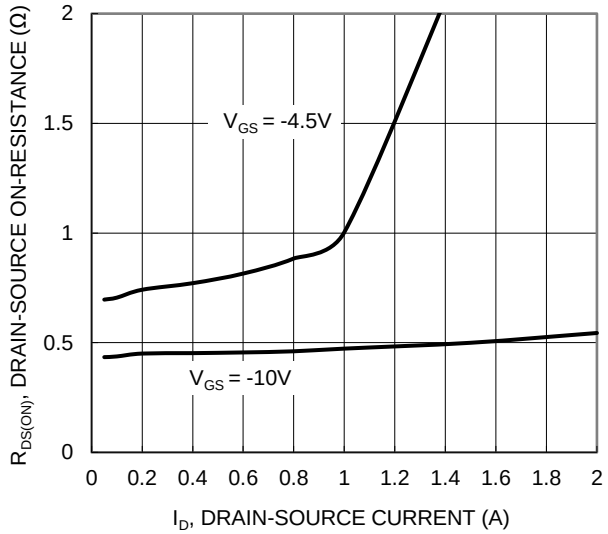


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

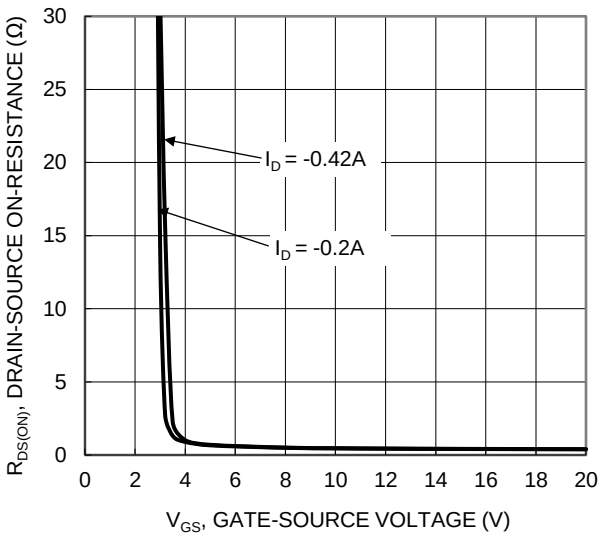


Figure 4. Typical Transfer Characteristic

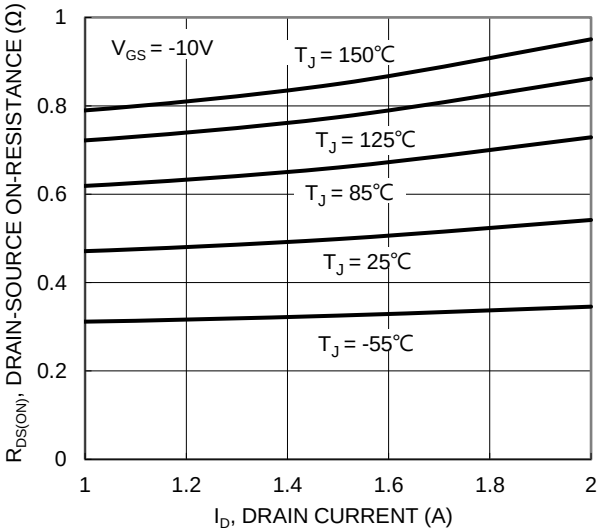


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

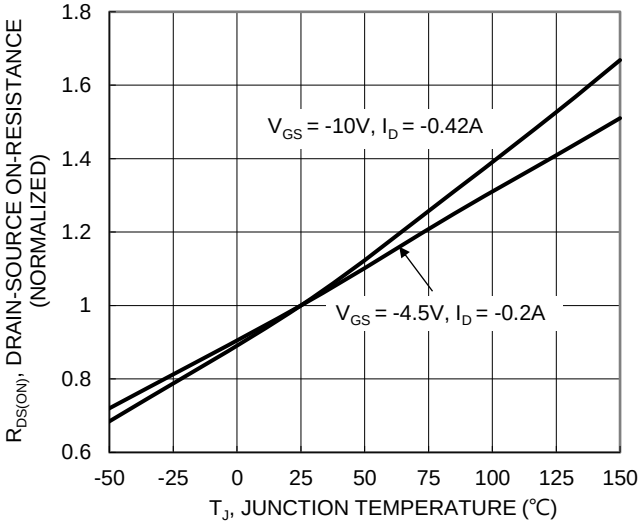


Figure 6. On-Resistance Variation with Junction Temperature

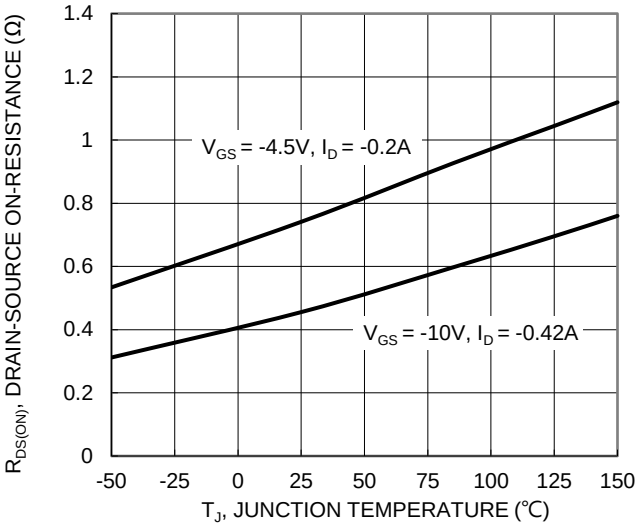


Figure 7. On-Resistance Variation with Junction Temperature

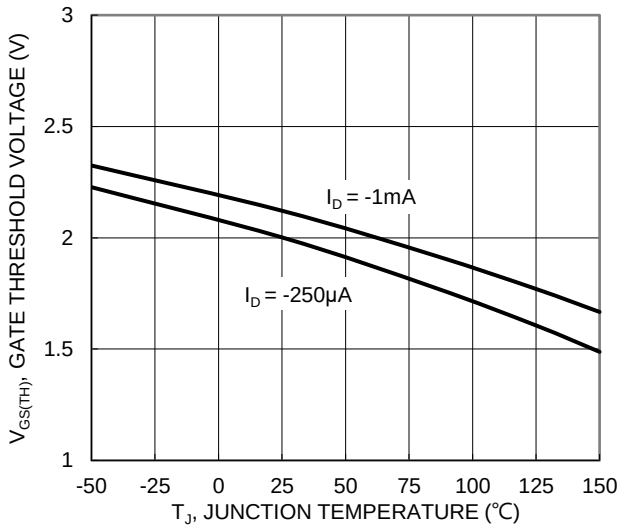


Figure 8. Gate Threshold Variation vs. Junction Temperature

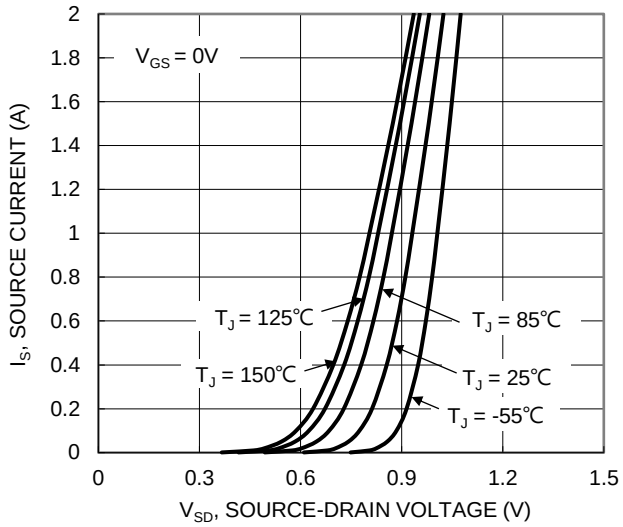


Figure 9. Diode Forward Voltage vs. Current

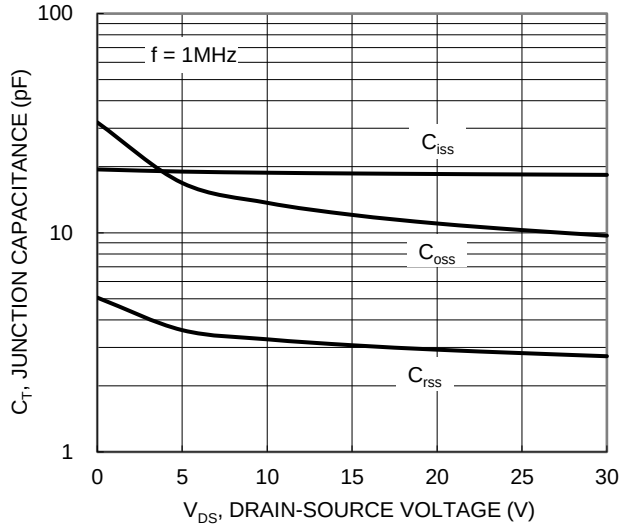


Figure 10. Typical Junction Capacitance

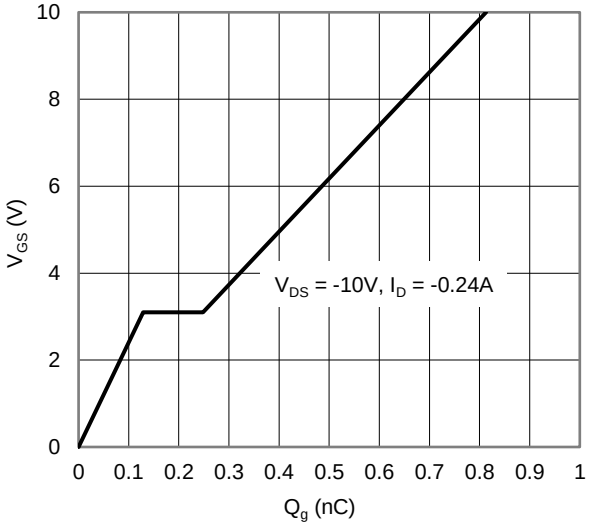


Figure 11. Gate Charge

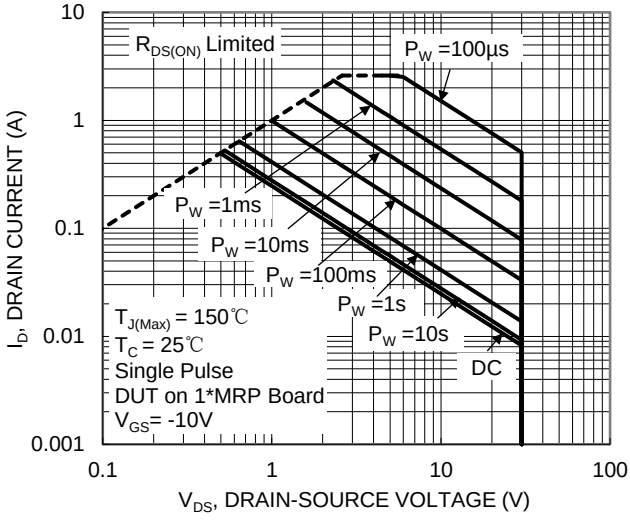


Figure 12. SOA, Safe Operation Area

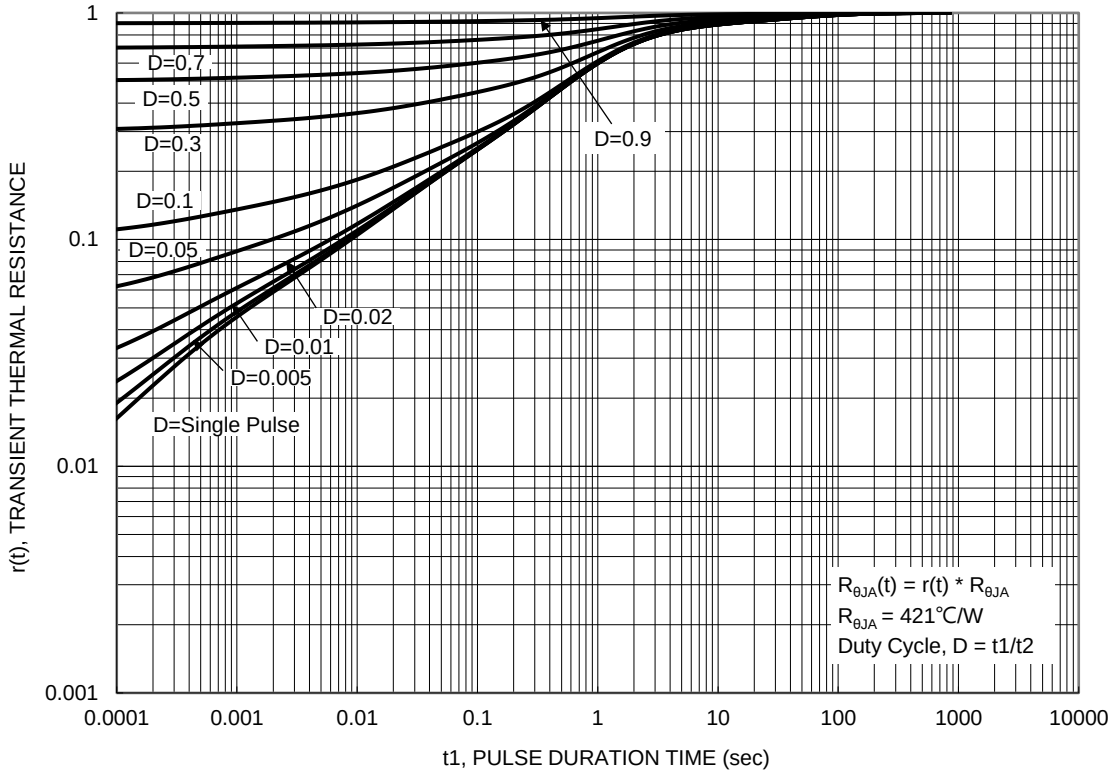
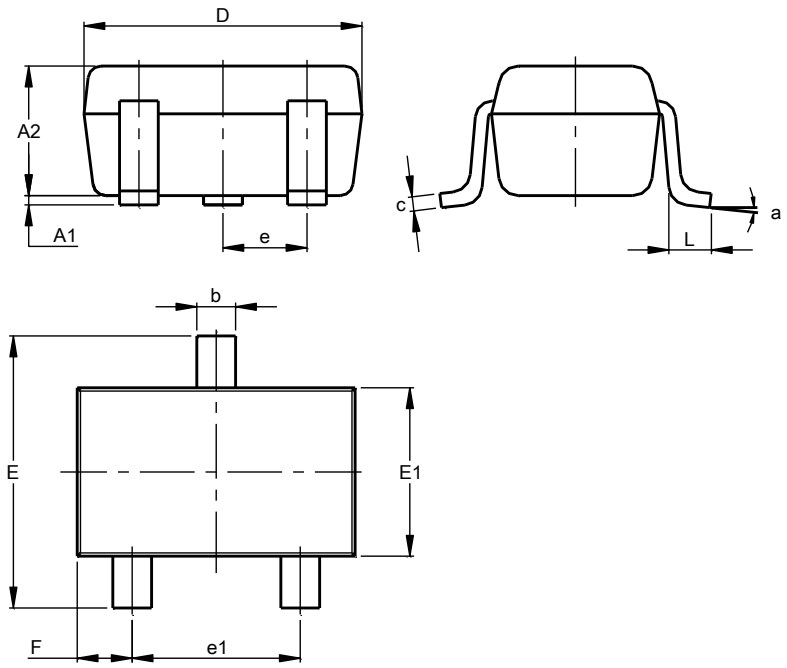


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

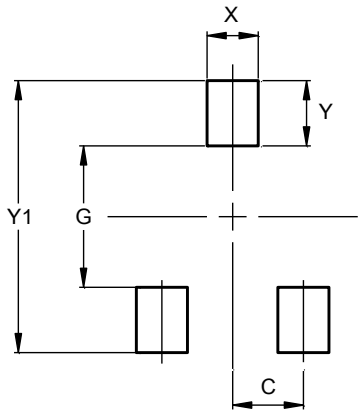
SOT323



SOT323			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500